Abstracts

A K band DRO in coplanar layout with dry and wet etched InP HEMTs

H.C. Duran, U. Lott, H. Benedickter and W. Bachtold. "A K band DRO in coplanar layout with dry and wet etched InP HEMTs." 1998 MTT-S International Microwave Symposium Digest 98.2 (1998 Vol. II [MWSYM]): 861-864.

A DRO operating in the frequency range of 23.2-24.8 GHz was designed using InGaAs-InAlAs-InP HEMTs with dry and wet etched gate recess. The oscillator consisted of an MMIC in coplanar waveguide technology and an externally coupled mechanically tunable DR mounted on a microstrip line. An output power of 12 dBm and a phase noise of -107 dBc/Hz at 100 kHz offset from the carrier were measured. The achieved power efficiency was 21%.

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